

1 23. (New) The polishing pad of Claim 22, wherein the circular base layer  
2 comprises at least two concentric annular regions, each of the at least two base  
3 layer concentric annular regions disposed so as to underlie a corresponding one  
4 of the at least two polishing regions.

1 24. (New) The polishing pad of Claim 23, wherein each of the at least two base  
2 layer concentric annular regions has a hardness that is different from the others  
3 of the at least two base layer concentric annular regions.

1 25. (New) The polishing pad of Claim 23, wherein each of the at least two base  
2 layer concentric annular regions has a thickness that is different from the others  
3 of the at least two base layer concentric annular regions.

61 Cont  
1 26. (New) The polishing pad of Claim 22, wherein the circular top layer ,  
2 comprises at least two concentric annular regions, each of the at least two top  
3 layer concentric annular regions disposed so as to correspond with a single one  
4 of the at least two polishing regions; and each of the at least two top layer  
5 concentric annular regions having different polishing characteristics.

1 27. (New) The polishing pad of Claim 22, wherein the circular top layer  
2 comprises at least two concentric annular regions, each of the at least two top  
3 layer concentric annular regions disposed so as to correspond with a single one  
4 of the at least two polishing regions; and each of the at least two top layer  
5 concentric annular regions having different surface textures.

1 28. (New) The polishing pad of Claim 22, wherein the at least two polishing  
2 regions are each of a size such that the wafer can be frictionally engaged with  
3 one of the at least two concentric annular polishing regions without  
4 simultaneously being engaged with others of the at least two concentric annular  
5 polishing regions.

1 29. (New) A polishing pad suitable for chemical mechanical polishing of wafers,  
2 comprising:

3 a linear base layer and an overlying linear top layer, the overlying linear  
4 top layer forming the polishing surface of the polishing pad;

5 wherein the polishing surface of the polishing pad has at least two  
6 polishing regions thereon, the at least two polishing regions having distinct  
7 polishing characteristics, and wherein the at least two polishing regions are  
8 disposed on the polishing pad as parallel linear regions.

1 30. (New) The polishing pad of Claim 29, wherein the at least two polishing  
2 regions are each of a size such that the wafer can be frictionally engaged with  
3 one of the at least two parallel linear polishing regions without simultaneously  
4 being engaged with others of the at least two parallel linear polishing regions.

1 31. (New) The polishing pad of Claim 29, wherein the linear base layer  
2 comprises at least two parallel linear regions, each of the at least two base layer  
3 parallel linear regions disposed so as to underlie a corresponding one of the at  
4 least two polishing regions.

1 32. (New) The polishing pad of Claim 31, wherein each of the at least two base  
2 layer parallel linear regions has a hardness that is different from the others of the  
3 at least two base layer parallel linear regions.

1 33. (New) The polishing pad of Claim 31, wherein each of the at least two base  
2 layer parallel linear regions has a thickness that is different from the others of the  
3 at least two base layer parallel linear regions.

1 34. (New) The polishing pad of Claim 29, wherein the linear top layer comprises  
2 at least two parallel linear regions, each of the at least two top layer parallel  
3 linear regions disposed so as to correspond with a single one of the at least two  
4 polishing regions; and each of the at least two top layer parallel linear regions  
5 having different polishing characteristics.

1 35. (New) The polishing pad of Claim 29, wherein the linear top layer comprises  
2 at least two parallel linear regions, each of the at least two top layer parallel  
3 linear regions disposed so as to correspond with a single one of the at least two  
4 polishing regions; and each of the at least two top layer parallel linear regions  
5 having different surface textures.